

IN THE CLAIMS:

Please delete Claims 2, 15. Furthermore, please enter the following clean version of amend Claims 1, 3, 7, 14, 16, 17, 19, and 20:

B1 1. A method of fabricating an electronic device formed on a semiconductor wafer, comprising the steps of:

forming a layer of a first material in a fixed position relative to the wafer, wherein the first material has a dielectric constant less than 3.6;

5 forming a photoresist layer in a fixed position relative to the layer of the first material;

forming at least one void through the layer of the first material in response to the photoresist layer, thereby forming a polymeric residue in response to the photoresist layer ;

10 subjecting the semiconductor wafer to a plasma which incorporates a gas which includes hydrogen so as to remove the photoresist layer; and

removing the polymeric residue, the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of hydrogen, oxygen, and fluorine.

B2 3. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a wet etch chemistry.

B3 7. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a combination of dilute hydrofluoric acid and an organic acid.

B4 14. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a dry plasma.

B5 16. The method of claim 1:
wherein the hydrogen in the mixture is provided from a hydrogen source selected from a group consisting of H_2 , NH_3 , N_2H_2 , H_2S , and CH_4 ; and
wherein the fluorine in the mixture is provided from a fluorine source selected
5 from a group consisting of CF_4 , C_2F_6 , CHF_3 , CH_2F_2 , SF_6 , CH_3F , and NF_3 .

17. The method of claim 1 wherein the mixture further comprises an inert gas.

B6 19. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of at least 50% hydrogen, and approximately 2-20% oxygen and approximately 2-6% fluorine.

20. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of approximately 80% NH_3 , approximately 10-15% N_2 , approximately 2-7% O_2 , and approximately 2-6% CF_4 .